

**SEMITOP® 3**

## IGBT Module

**SK25MLI065**

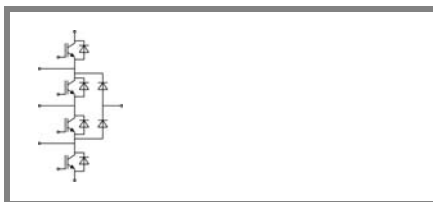
Target Data

### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast NPT IGBT technology
- CAL technology FWD

### Typical Applications\*

- Multi level inverter



MLI

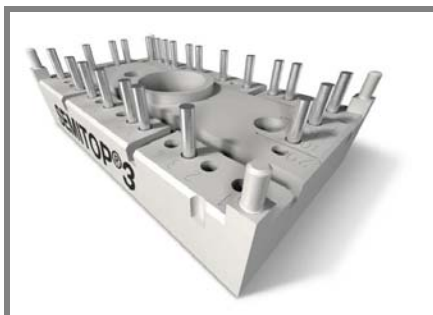
Absolute Maximum Ratings		$T_s = 25\text{ °C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT</b>			
$V_{CES}$	$T_j = 25\text{ °C}$	600	V
$I_C$	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	30 A
		$T_s = 80\text{ °C}$	22 A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	60	A
$V_{GES}$		$\pm 20$	V
$t_{psc}$	$V_{CC} = 300\text{ V}$ ; $V_{GE} \leq 20\text{ V}$ ; $T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	10	$\mu\text{s}$

<b>Inverse Diode</b>			
$I_F$	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	36 A
		$T_s = 80\text{ °C}$	24 A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$		A
$I_{FSM}$	$t_p = 10\text{ ms}$ ; half sine wave $T_j = 150\text{ °C}$	200	A

<b>Freewheeling Diode</b>			
$I_F$	$T_j = 150\text{ °C}$	$T_{case} = 25\text{ °C}$	36 A
		$T_{case} = 80\text{ °C}$	24 A
$I_{FRM}$			A
$I_{FSM}$	$t_p = 10\text{ ms}$ ; half sine wave $T_j = 150\text{ °C}$	200	A

<b>Module</b>			
$I_{t(RMS)}$			A
$T_{vj}$		-40 ... +150	$^{\circ}\text{C}$
$T_{stg}$		-40 ... +125	$^{\circ}\text{C}$
$V_{isol}$	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 0,7\text{ mA}$	3	4	5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = V_{CES}$ $T_j = 25\text{ °C}$			0,0022	mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = 20\text{ V}$ $T_j = 25\text{ °C}$			120	nA
$V_{CE0}$		$T_j = 25\text{ °C}$	1,4	1,9	V
		$T_j = 125\text{ °C}$	1,7	2,2	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$			$\text{m}\Omega$
		$T_j = 125\text{ °C}$	44		$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 30\text{ A}$ , $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,8		V
		$T_j = 125\text{ °C}_{chiplev.}$	2,1		V
$C_{ies}$	$V_{CE} = 25$ , $V_{GE} = 0\text{ V}$ $f = 1\text{ MHz}$		1,6		nF
$C_{oes}$		0,15		nF	
$C_{res}$		0,09		nF	
$t_{d(on)}$	$R_{Gon} = 33\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 25\text{ A}$	30		ns
$t_r$			25		ns
$E_{on}$	$R_{Goff} = 33\ \Omega$	$T_j = 125\text{ °C}$ $V_{GE} = \pm 15\text{ V}$	0,75		mJ
$t_{d(off)}$			250		ns
$t_f$			15		ns
$E_{off}$			0,6		mJ
$R_{th(j-s)}$	per IGBT			1,4	K/W



**SEMITOP<sup>®</sup> 3**

## IGBT Module

**SK25MLI065**

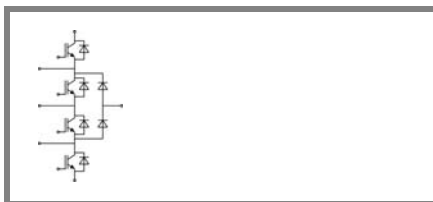
### Target Data

### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast NPT IGBT technology
- CAL technology FWD

### Typical Applications\*

- Multi level inverter

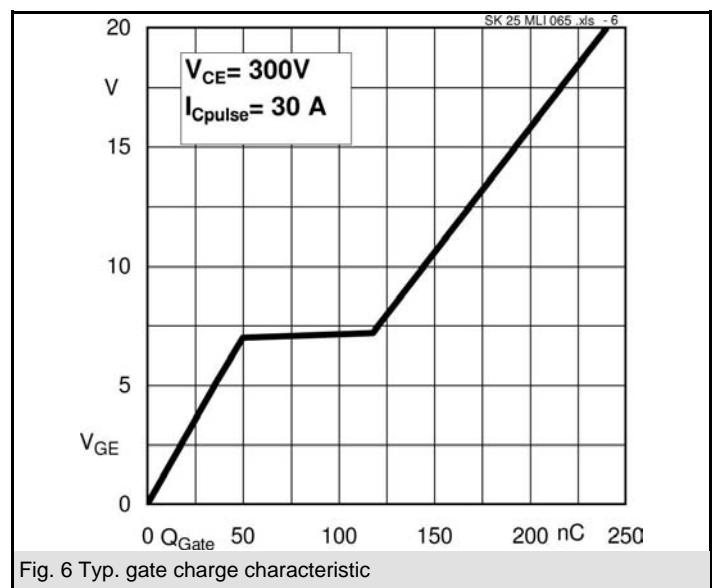
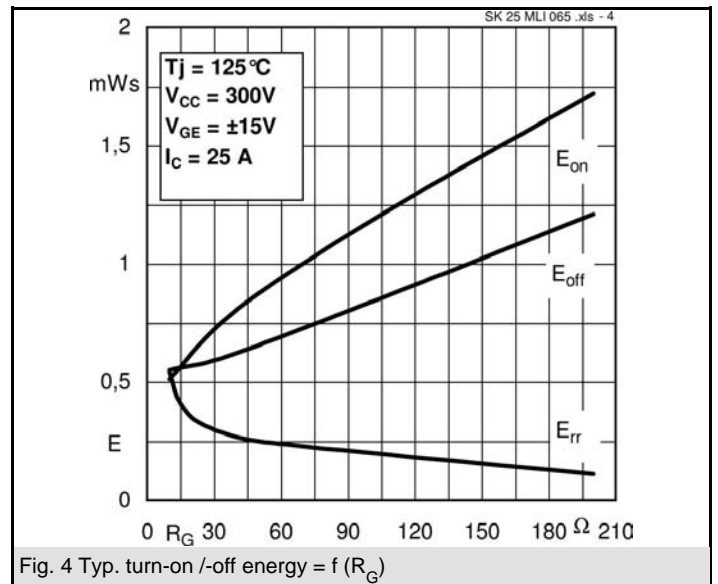
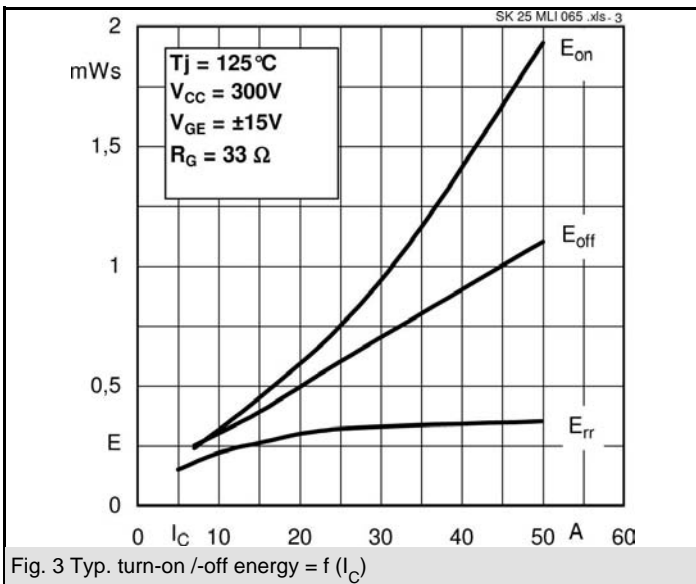
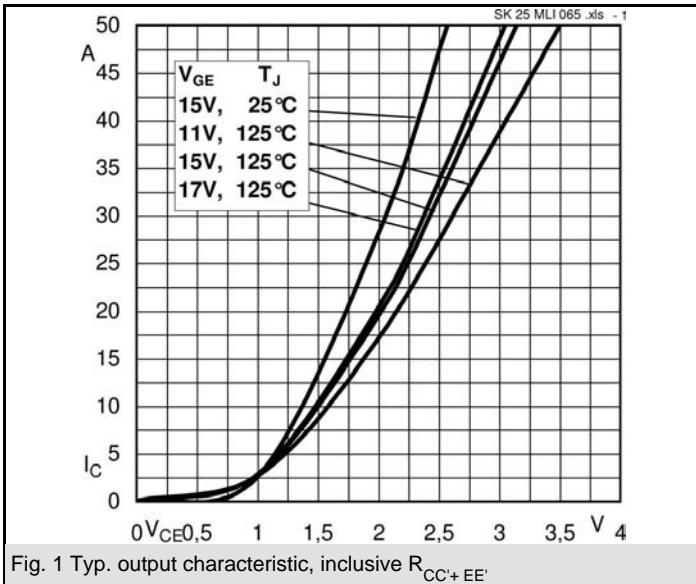


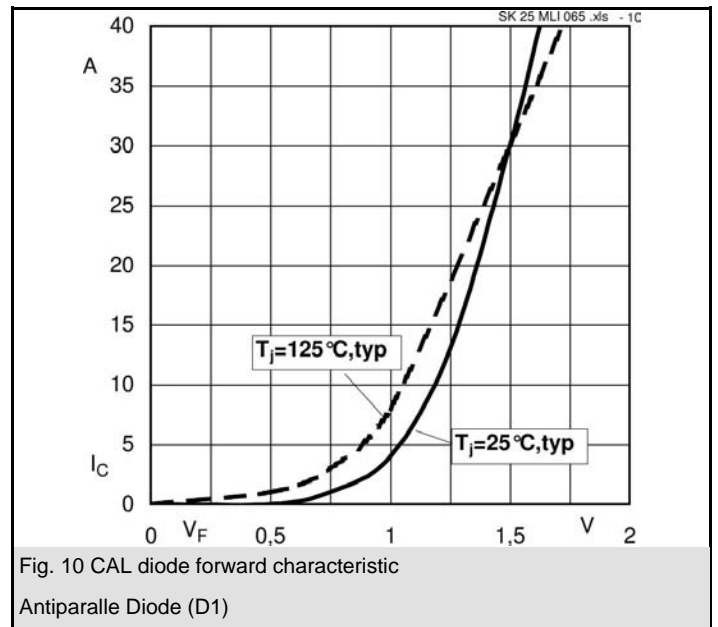
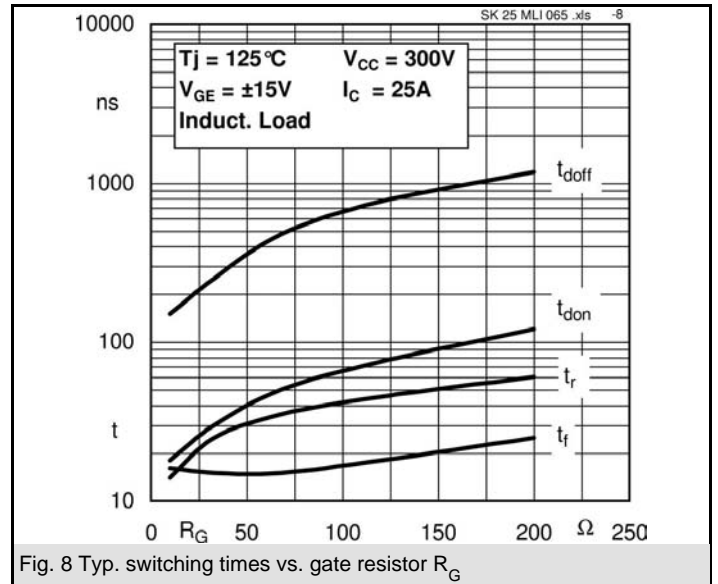
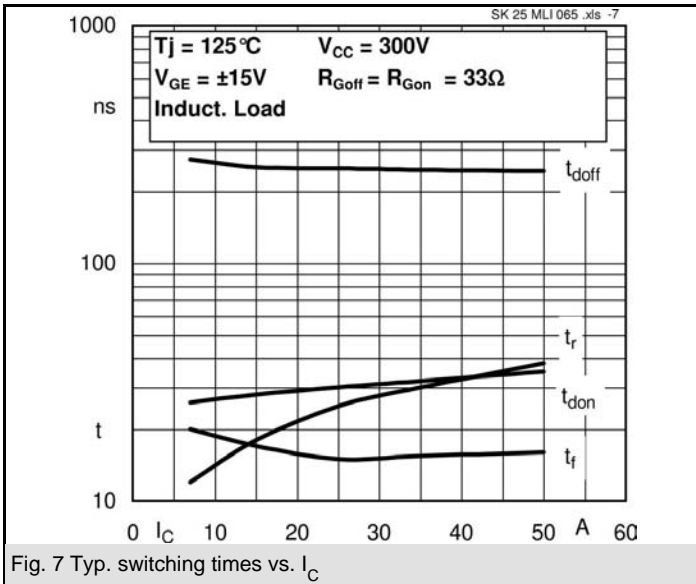
**MLI**

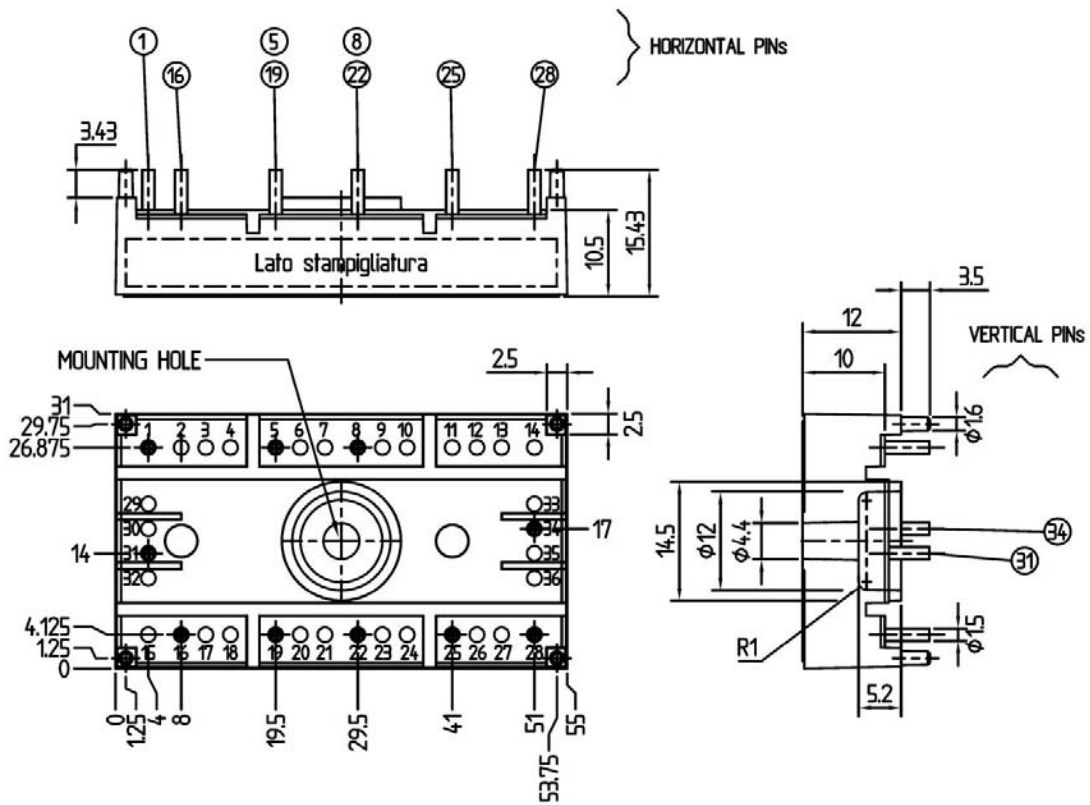
Characteristics							
Symbol	Conditions			min.	typ.	max.	Units
<b>Antiparallel Diode (D1)</b>							
$V_F = V_{EC}$	$I_{Fnom} = 25 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$			1,45		V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$			1,4		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$					V
		$T_j = 125 \text{ }^\circ\text{C}$			0,85		V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$					mΩ
		$T_j = 125 \text{ }^\circ\text{C}$			22		mΩ
$I_{RRM}$	$I_F = 25 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$					A
$Q_{rr}$	$di/dt = -2400 \text{ A}/\mu\text{s}$						μC
$E_{rr}$	$V_R = 300\text{V}$				0,32		mJ
$R_{th(j-s)D}$	per diode					1,7	K/W
<b>Freewheeling Diode (D2)</b>							
$V_F = V_{EC}$	$I_{Fnom} = 25 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$			1,45		V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$			1,4		V
$V_{F0}$		$T_j = 125 \text{ }^\circ\text{C}$			0,85		V
$r_F$		$T_j = 125 \text{ }^\circ\text{C}$			22		V
$I_{RRM}$	$I_F = 25 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$					A
$Q_{rr}$	$di/dt = -2400 \text{ A}/\mu\text{s}$						μC
$E_{rr}$	$V_R = 300\text{V}$				0,32		mJ
$R_{th(j-s)FD}$	per diode					1,7	K/W
$M_s$	to heat sink			2,25		2,5	Nm
w					30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

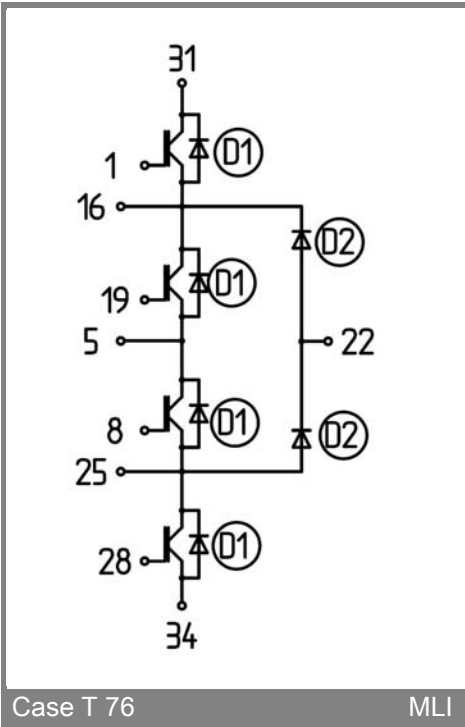
\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T 76 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 76

MLI